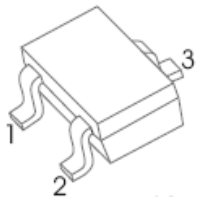
SS8050W *TRANSISTOR (NPN)*

SOT－323



1. BASE
2. EMITTER
3. COLLECTOR

FEATURES

Complimentary to SS8550W

MARKING: Y1

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	40	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	1.5	A
P_C	Collector Power Dissipation	0.2	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

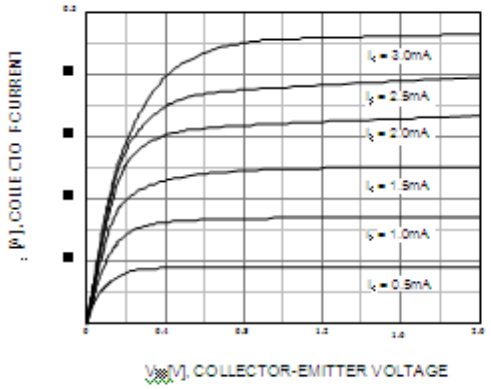
Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C= 100μA, I_E=0	40			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 0.1mA, I_B=0	25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	5			V
Collector cut-off current	I_{CBO}	V_{CB}=40V, I_E=0			0.1	μA
Collector cut-off current	I_{CEO}	V_{CB}=20V, I_E=0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V, I_C=0			0.1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=1V, I_C= 100mA	120		400	
	$h_{FE(2)}$	V_{CE}=1V, I_C= 800mA	40			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=800mA, I_B= 80mA			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=800mA, I_B= 80mA			1.2	V
Transition frequency	f_T	V_{CE}=10V, I_C= 50mA f=30MHz	100			MHz

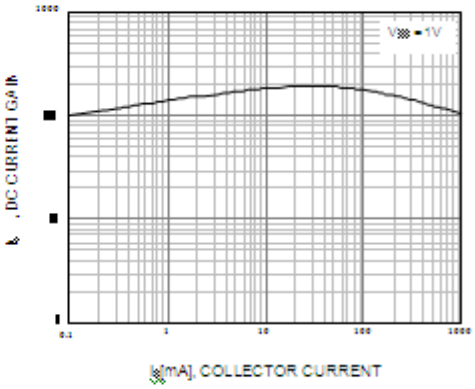
CLASSIFICATION OF $h_{FE(1)}$

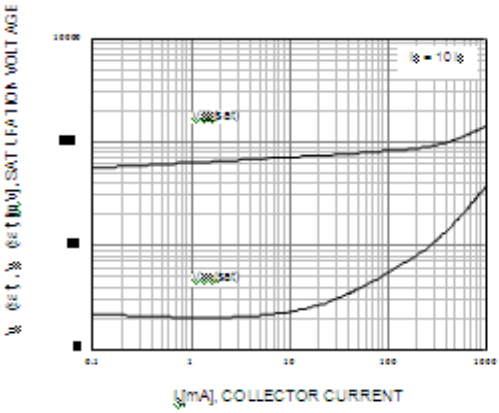
RANK	L	H	J
RANGE	120－200	200－350	300－400

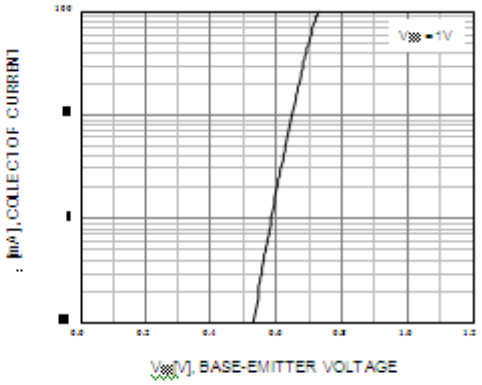
Typical Characteristics

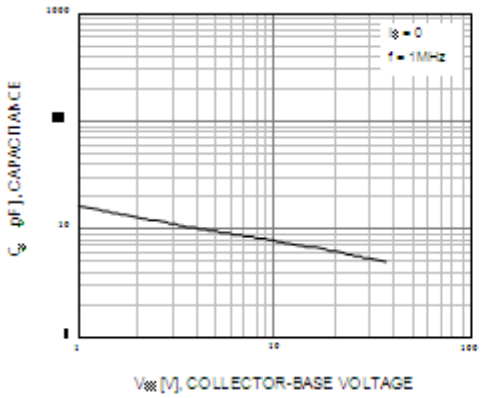
SS8050W

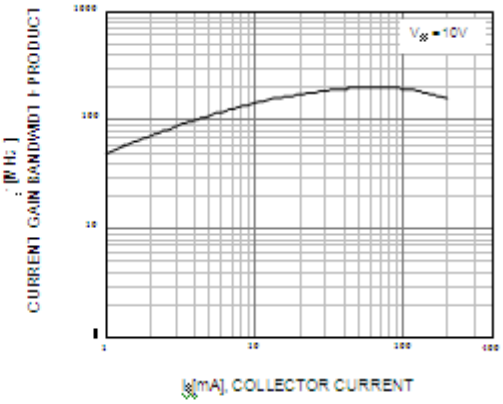




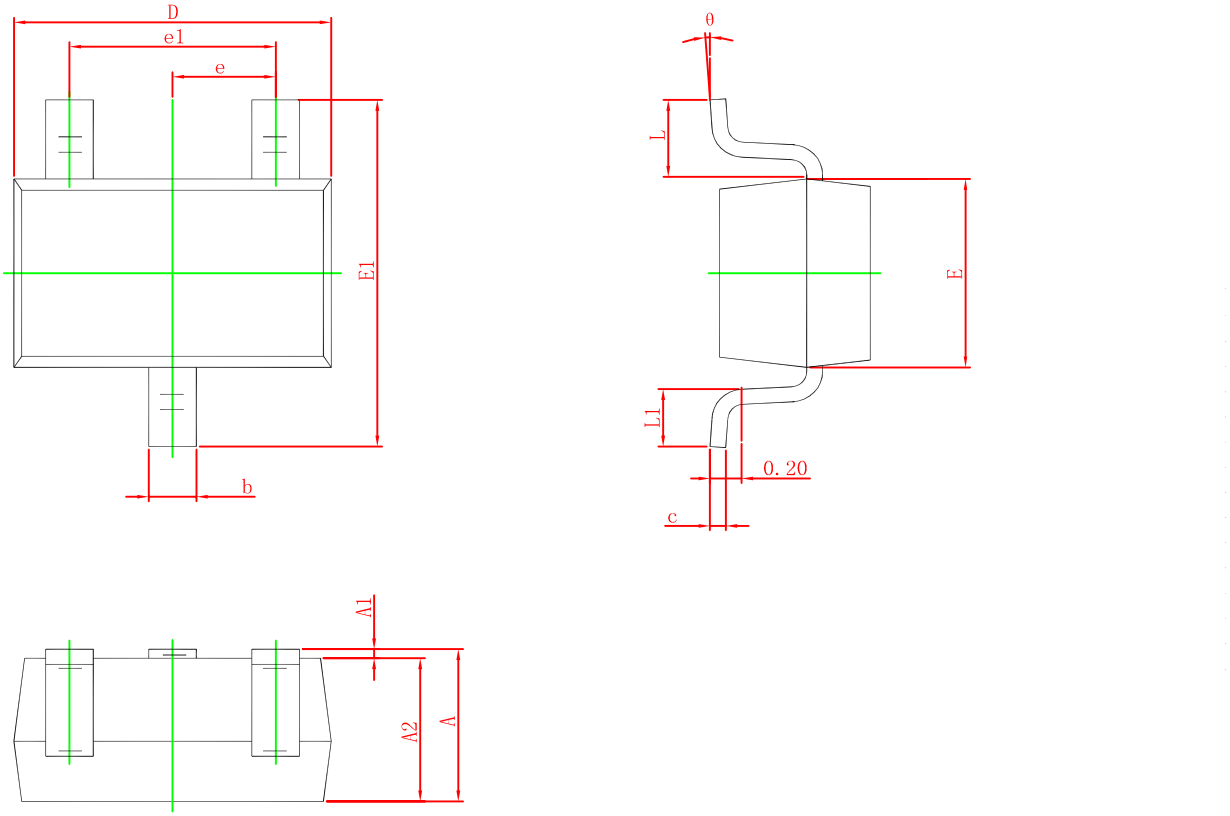








SOT-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°